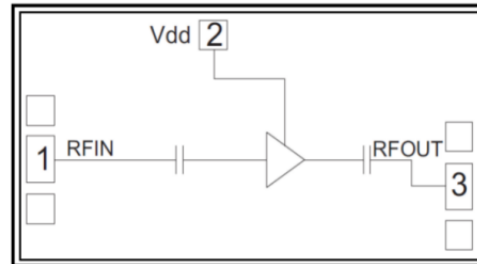


Features

- Single Biasing Voltage (Self Biased)
- Frequency: 26-40GHz
- Small Signal Gain: 21dB (positive slope)
- Noise Figure: 2.0dB typ. / 2.1dB max.
- P1dB: 3dBm
- Power Supply: +5 V/12 mA
- Input/Output: 50Ω
- Die Size: 1.6 x 0.8 x 0.09 mm

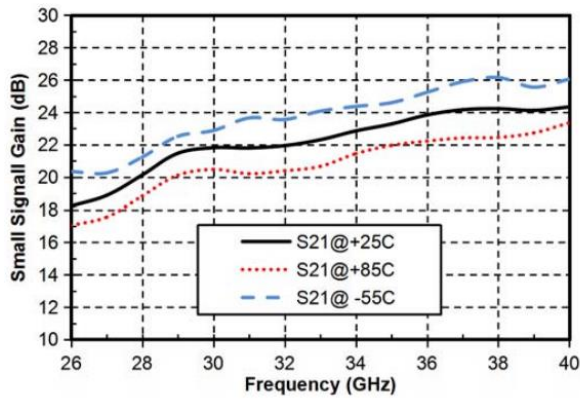
Functional Block Diagram

Typical Applications

- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

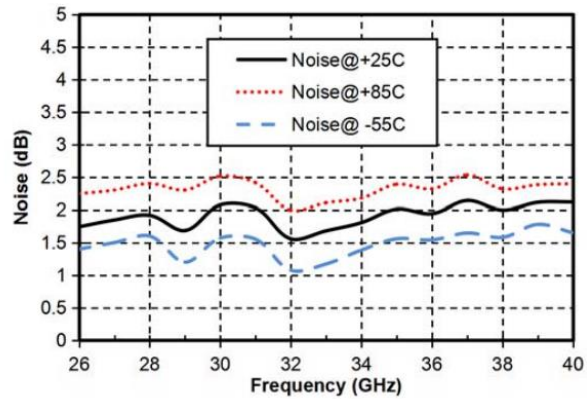
Electrical Specifications
TA = +25°C, Vd = +5V

Parameters	Min.	Typ.	Max.	Units
Frequency	26-40			GHz
Small Signal Gain	17	21	24.5	dB
Gain Flatness		±4		dB
Noise Figure	1.7	2.0	2.1	dB
Output 1dB Compression (P1dB)	2	3	5	dBm
Saturated Output Power (Psat)	3.5	5	6.5	dBm
Input Return Loss	10	13	-	dB
Output Return Loss	10	14	-	dB
Static current		12		mA

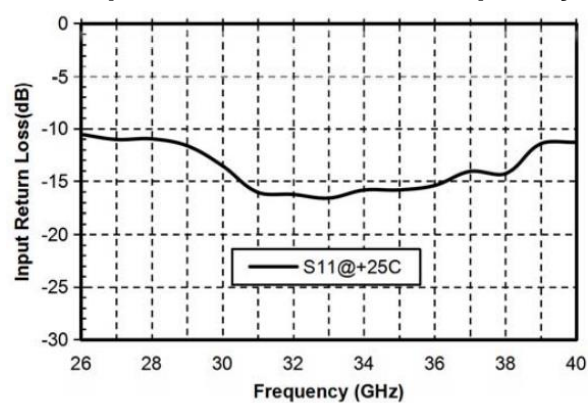
Gain vs. Temperature



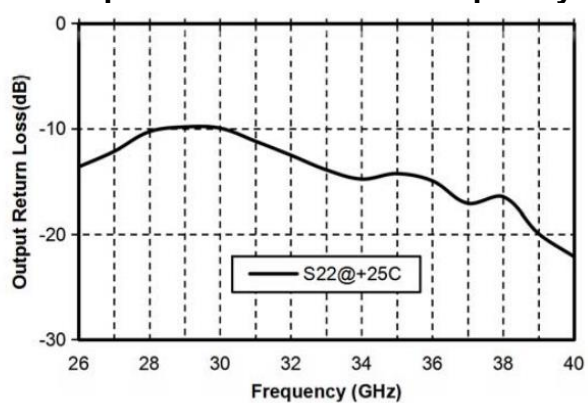
Noise Figure vs. Temperature



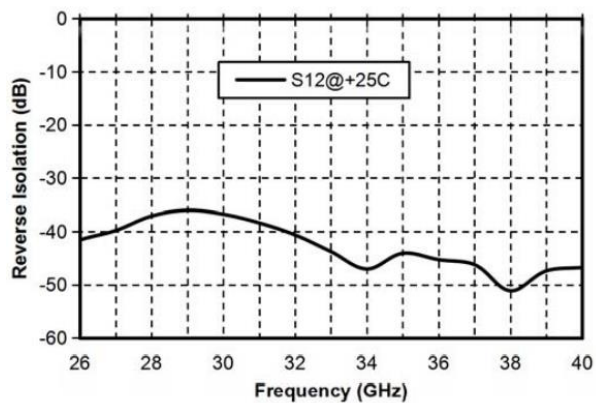
Input Return Loss vs. Frequency



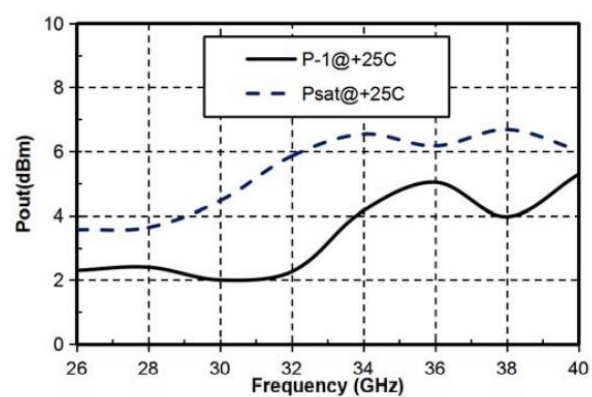
Output Return Loss vs. Frequency



Reverse Isolation vs. Frequency

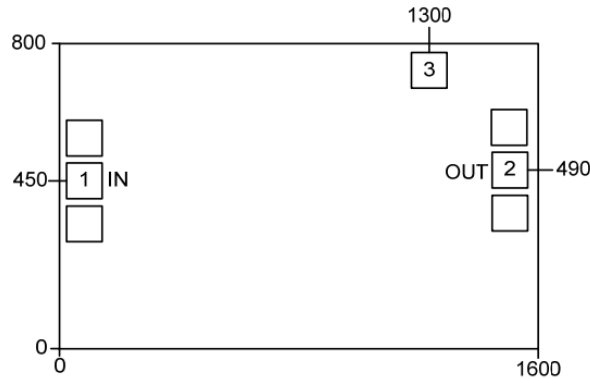


P1dB. Psat vs. Frequency





Outline Drawing: All Dimensions in μm

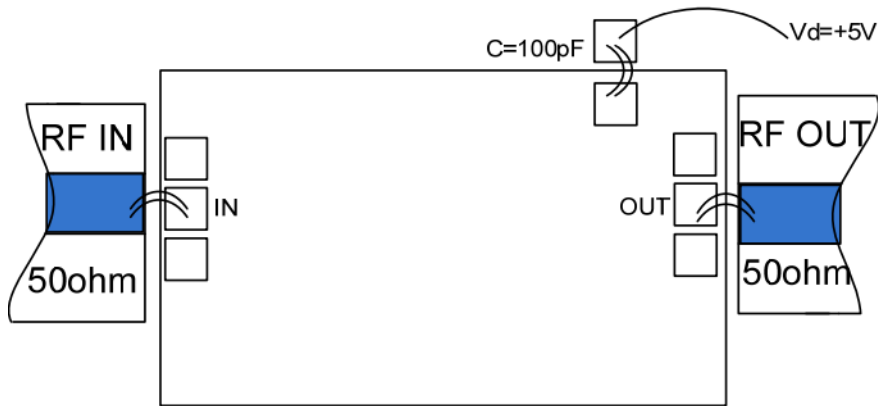


Pad Description

Pad	Function	Description
1	RF IN	RF signal input terminal, no blocking capacitor required.
2	RF OUT	RF signal output terminal, no blocking capacitor required.
3	Vd	Amplifier drain bias; external 100pF bypass capacitor required.
Die bottom	GND	Die bottom must be connected to RF/DC ground.



Assembly Drawing



Notes:

1. Die thickness: 100um
2. Typical bond pad is 100*100 μm^2
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:

1. Maximum drain voltage: +7V
2. Maximum input power: +20dBm
3. Operating temperature: -55°C to +85°C
4. Storage temperature: -65°C to +150°C